

## **Errata: Properties of Step-Edge Pb–Si–Pb Josephson Junctions\***

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(Received November 5, 1986)

Equation (1) should read

$$R_n = (\pi/\sigma w)[\ln(8k/L)]^{-1}$$

In Eq. (3) the device length  $L$  was called  $a$  to correspond to the notation of Ref. 15.

In Fig. 4 the critical current is scaled using  $J_c/B(6k_B/\pi\hbar\tau)^{1/2}$  and not  $J_c/B(6k_B/\pi\hbar\tau)$  as mentioned in the text.

\*This paper appeared in *J. Low Temp. Phys.* **63**, 23 (1986).